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RLT8410G TECHNICAL DATA



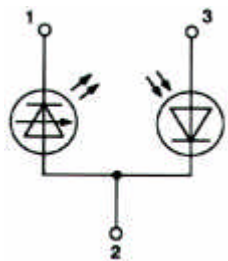
High Power Infrared Laserdiode

Structure: **AlGaAs/GaAs**
 Lasing wavelength: **840 nm typ.**
 Max. optical power: **10 mW, single mode**
 Package: **9 mm**

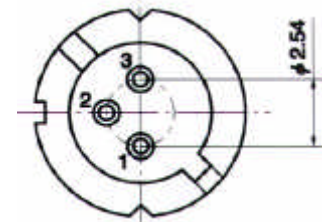
NOTE!
 LASERDIODE
 MUST BE COOLED!



PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	15	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	5	V
Operating Temperature	T _C	-50 .. +60	°C
Storage Temperature	T _{STG}	-60 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o			10		mW
Threshold Current	I _{th}		30	40	50	mA
Operation Current	I _{op}	P _o = 10 mW	40	60	80	mA
Lasing Wavelength	λ _p	P _o = 10 mW	830	840	850	nm
Beam Divergence	θ _{//}	P _o = 10 mW		12		°
Beam Divergence	θ _⊥	P _o = 10 mW		25		°
Differential Efficiency	dP _o /dI _{op}	P _o = 10 mW		0.75		mW/mA
Monitor Current	I _m	P _o = 10 mW	100	250	600	μA